

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A write-once memory device comprising a memory cell formed over an insulating surface, which includes a semiconductor film having two impurity regions and a region therebetween, a gate electrode formed over the region with an insulating film interposed therebetween, and two wirings connected to the respective impurity regions,

wherein the semiconductor film interposed between the two wirings of the memory cell is altered to an insulating state by applying a voltage between the gate electrode and at least one of the two wirings,

wherein a potential of the gate electrode is changed, and

wherein the gate electrode and the semiconductor film are formed in contact with the insulating film.

2. (Currently Amended) The write-once memory device according to claim 1, wherein each memory cell of the memory device comprises two or more gate electrodes on the same insulating film.

3. (Canceled)

4. (Currently Amended) A write-once memory device comprising a first memory cell and a second memory cell formed over an insulating surface, each of which includes a semiconductor film having two impurity regions and a region therebetween, a gate electrode formed over the region with an insulating film interposed therebetween, and two wirings connected to the respective impurity regions,

wherein the first memory cell comprises an initial state; and  
the semiconductor film interposed between the two wirings of the second memory cell is altered to an insulating state by applying a voltage between the gate electrode and at least one of the two wirings,  
wherein a potential of the gate electrode is changed, and  
wherein the gate electrode and the semiconductor film are in contact with the insulating film.

5. (Currently Amended) The write-once memory device according to claim 4, wherein each memory cell of the memory device comprises two or more gate electrodes on the same insulating film.

6. (Canceled)

7. (Currently Amended) A write-once memory device comprising a memory cell formed over an insulating surface, which includes a semiconductor film having one or two impurity regions, an electrode formed over the impurity region with an insulating film interposed therebetween, and two wirings connected to the respective impurity regions or two wirings connected to the one impurity region,

wherein the semiconductor film interposed between the two wirings of the memory cell is altered to an insulating state by applying a voltage between the gate electrode and at least one of the two wirings,  
wherein a potential of the gate electrode is changed, and  
wherein the gate electrode and the semiconductor film are in contact with the insulating film.

8. (Previously Presented) The write-once memory device according to claim 7, wherein the gate electrode is interposed between the two wirings.

9. (Currently Amended) The write-once memory device according to claim 7, wherein each memory cell of the memory device comprises two or more gate electrodes on the same insulating film.

10. (Canceled)

11. (Currently Amended) A write-once memory device comprising a first memory cell and a second memory cell formed over an insulating surface, each of which includes a semiconductor film having one or two impurity regions, an electrode formed over the impurity region with an insulating film interposed therebetween, and two wirings connected to the respective impurity regions or two wirings connected to the one impurity region,

wherein the first memory cell has an initial state; and

the semiconductor film interposed between the two wirings of the second memory cell is altered to an insulating state by applying a voltage between the gate electrode and at least one of the two wirings,

wherein a potential of the gate electrode is changed, and

wherein the gate electrode and the semiconductor film are in contact with the insulating film.

12. (Previously Presented) The write-once memory device according to claim 11, wherein the electrode is interposed between the two wirings.

13. (Currently Amended) The write-once memory device according to claim 11, wherein each memory cell of the memory device comprises two or more electrodes on the same insulating film.

14. (Canceled)

15. (Currently Amended) A manufacturing method of a write-once memory device, comprising the steps of:

forming an island shape semiconductor film over an insulating surface;

forming a gate insulating film over the island shape semiconductor film;

forming a gate electrode over the gate insulating film;

doping an N-type impurity element with the gate electrode used as a mask, thereby forming an N-type high concentration impurity region in the island shape semiconductor film;

forming an interlayer film over the gate insulating film and the gate electrode;

forming a contact hole in the interlayer film and a wiring connected to the high concentration impurity region, thereby forming a memory cell, and

applying a voltage between the gate electrode and the wiring of the memory cell, thereby altering a channel region of the island shape semiconductor film to an insulating state,

wherein a potential of the gate electrode is changed, and

wherein the gate electrode and the semiconductor film are in contact with the gate insulating film.

16. (Currently Amended) The method of a write-once memory device according to claim 15, wherein each memory cell of the memory device comprises two or more gate electrodes on the same insulating film.

17. (New) The write-once memory device according to claim 1, further comprising sidewalls formed on side surfaces of the gate electrode.

18. (New) The write-once memory device according to claim 4, further

comprising sidewalls formed on side surfaces of the gate electrode.

19. (New) The write-once memory device according to claim 7, further comprising sidewalls formed on side surfaces of the gate electrode.

20. (New) The write-once memory device according to claim 11, further comprising sidewalls formed on side surfaces of the gate electrode.

21. (New) The method of a write-once memory device according to claim 15, further comprising a step of forming sidewalls on side surfaces of the gate electrode.